

EDF65S06R1L

ev™ Silicon Carbide Schottky Diode
650V, 6A

Features

- Zero Reverse Recovery Current
- Low Forward Voltage
- High Surge Current Capability
- Independent of Temperature Switching Behavior
- Positive Temperature Coefficient
- Max Junction Temperature 175 °C
- Pb-free, Halogen Free, and RoHS Compliant

Benefits

- Higher Efficiency
- Ease of Paralleling
- Increased Power Density
- Reduced Cooling Requirements

Applications

- Solar Inverters
- Power Factor Correction
- Industrial Power Supply
- EV Charging Station

V_{RRM}	$I_F, T_C=25^\circ\text{C}$	$T_{J, \text{Max}}$	Q_C, Typ
650V	6A	175°C	17nC



Ordering Information

Part Number	Package	Shipping	Quantity
EDF65S06R1L	TO-220F-2L	Tube	50 units

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		650	V
I_F	Forward Current	$T_C=110^\circ\text{C}$	6	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	$T_C=25^\circ\text{C}, t_p=10\text{ms}$	26	A
		$T_C=150^\circ\text{C}, t_p=10\text{ms}$	22	
$I_{F,Max}$	Non-Repetitive Peak Forward Current	$T_C=25^\circ\text{C}, t_p=10\mu\text{s}$	290	A
		$T_C=150^\circ\text{C}, t_p=10\mu\text{s}$	247	
I^2dt value	$\int I^2 dt$	$T_C=25^\circ\text{C}, t_p=10\text{ms}$	3.3	A^2s
		$T_C=150^\circ\text{C}, t_p=10\text{ms}$	2.4	A^2s
P_{tot}	Power Dissipation	$T_C=25^\circ\text{C}$	29	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to 175	°C

■ Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	5.2	°C/W

■ Electrical Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=6A, T_J=25^{\circ}C$		1.50	1.80	V
		$I_F=6A, T_J=175^{\circ}C$		1.65		
I_R	Reverse Current	$V_R=650V, T_J=25^{\circ}C$			100	μA
		$V_R=650V, T_J=175^{\circ}C$			300	
Q_C	Total Capacitive Charge	$V_R=400V, T_J=25^{\circ}C$		17		nC
C	Total Capacitance	$V_R=1V, f=100kHz$		273		pF
		$V_R=400V, f=100kHz$		24		
E_C	Capacitance Stored Energy	$V_R=400V$		2.4		μJ

■ Typical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Figure 1. Forward Characteristics

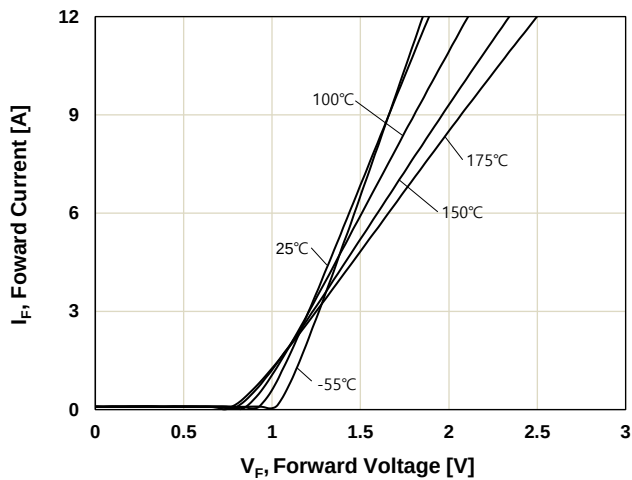


Figure 2. Reverse Characteristics

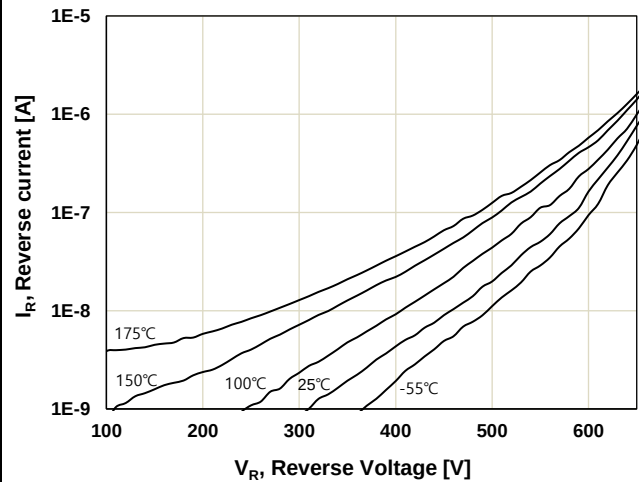


Figure 3. Power Derating

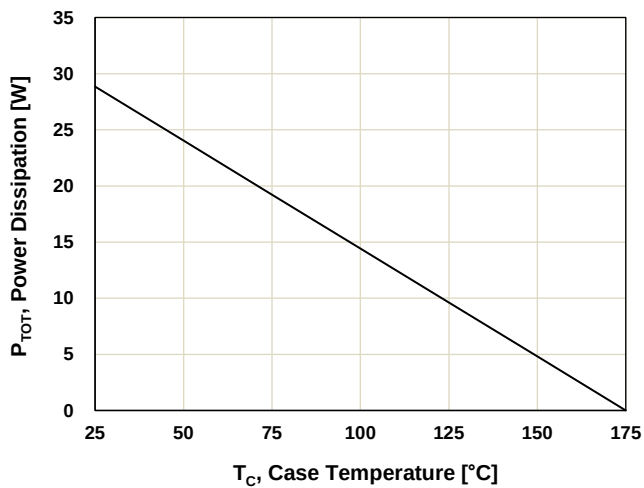


Figure 4. Current Derating

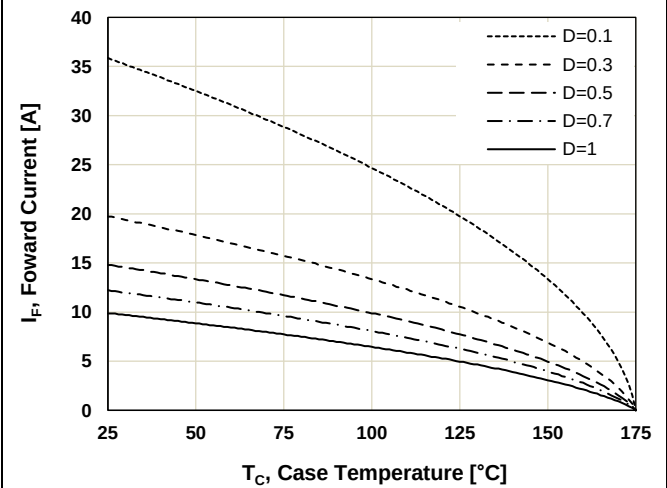


Figure 5. Capacitive Charge Characteristics

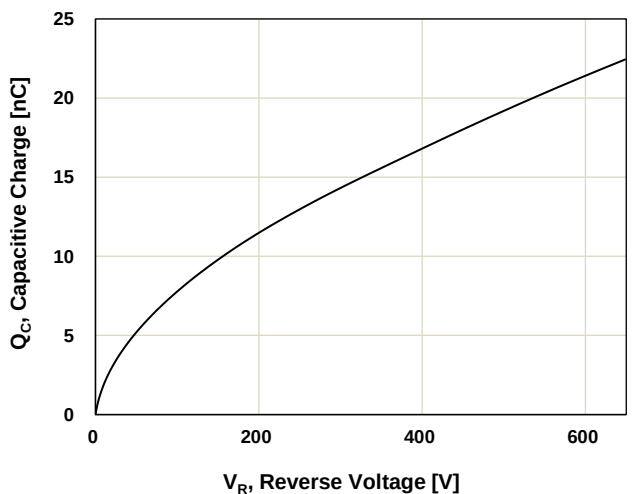
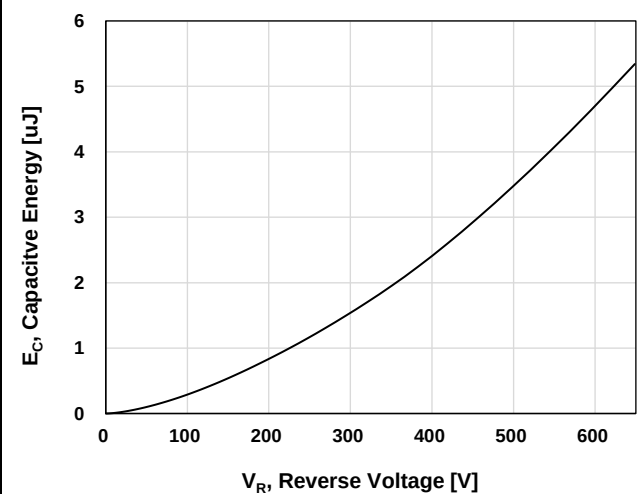


Figure 6. Capacitance Stored Energy



■ Typical Characteristics

Figure 7. Capacitive Characteristics

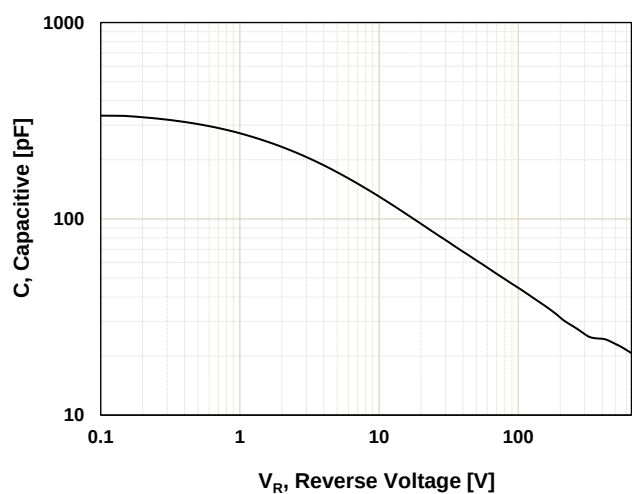
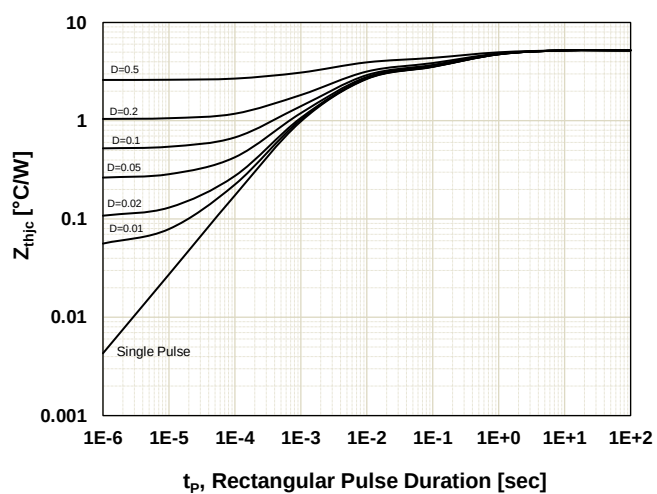
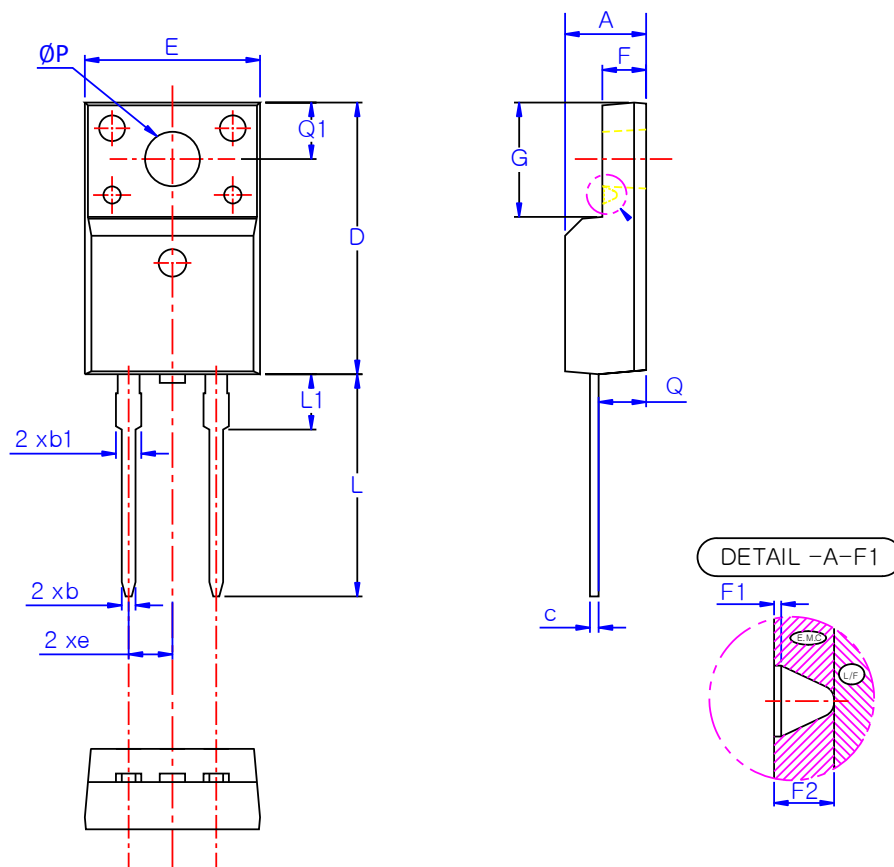


Figure 8. Transient Thermal Response Curve



Package Outlines

TO-220F-2L



SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.90
b	0.70	0.80	0.90
b1	1.33	1.40	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
E	9.96	10.16	10.36
e	2.54 BSC		
F	2.34	2.54	2.74
	(0.10)		
F2	(0.84)		
G	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
Q	2.56	2.76	2.96
Q1	3.10	3.30	3.50
ØP	3.08	3.18	3.28

NOTE

1. THESE DIMENSIONS DO NOT INCLUDE PROTRUSIONS OF THE MOLD.
2. THE "()" MARK IS THE REFERENCE.

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